

IC Stage Biasing

- *Avoids resistors as much as possible*
 - *Resistors take up very large area on IC chips, which is at a premium*
- *Uses transistors as biasing elements*
 - *Much more compact than resistors, and area consumption is almost negligible as compared to resistors*
- Also known as *active biasing*

- **Parameters:**

- **Output Current I_0**

- *As per specification*

- **Output Resistance R_0**

- $R_0 = \Delta V_0 / \Delta I_0 = dV_0 / dI_0 = v_0 / i_0$ (**ac**)
- *As large as possible - ideally infinite*

- **Minimum Allowed Output Voltage $V_{0,min}$**

- *As small as possible - ideally zero*
- **Dictated by:**
 - ❖ **For BJT:** $V_{CE(min)} = V_{CE(SS)} = 0.2 \text{ V}$
 - ❖ **For MOSFET:** $V_{DS(min)} = V_{GT(min)} = 80 \text{ mV}$

- *I_0 should be independent of power supply and temperature*
 - *Temperature and Supply Independent Biasing*
- *Should use minimum number of circuit elements*
 - *Economization of space*
- *Should not affect frequency response*
- It is *almost impossible to satisfy all these constraints simultaneously*
 - *Look for optimization*

Current Sources/Sinks

- Also known as *Current Mirrors* (CM)
- Can be used for *biasing* as well as *load elements* (known as *active load*)
- Designed based on *required specifications*
- *Two sources of errors:*
 - *Systematic: Even when devices are matched*
 - *Random: When there is a random mismatch between devices*

- *Simple npn CM:*

- Q_1 has its *B and C shorted*

- *Can never saturate* ($V_{BC} = 0$)
- Known as *diode-connected BJT*

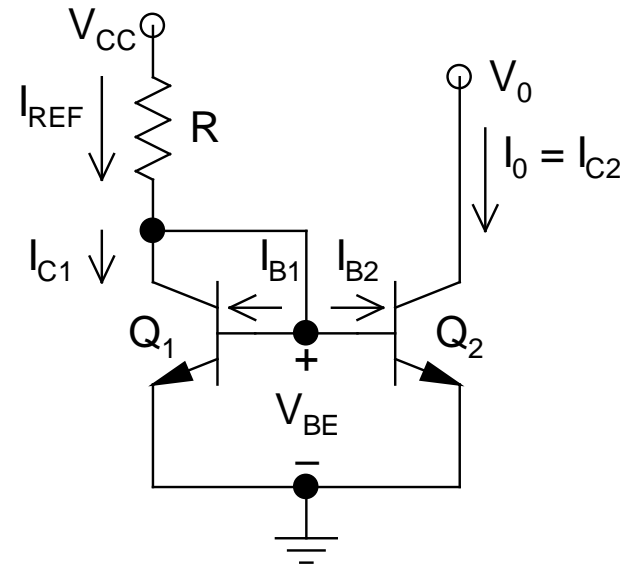
- Q_1 and Q_2 have *same V_{BE}*

- $I_{REF} = \text{Reference Current}$
 $= (V_{CC} - V_{BE})/R$

- $I_0 = \text{Output Current} = I_{C2}$

- $V_0 = \text{Output Voltage}$

- *Variable, depends on the load connected to it*



➤ *General Analysis:*

$$I_{\text{REF}} = I_{\text{C1}} + I_{\text{B1}} + I_{\text{B2}} = I_{\text{C1}} \left(1 + \frac{1}{\beta_1} \right) + \frac{I_{\text{C2}}}{\beta_2}$$

➤ Now:

$$V_{\text{BE}} = V_{\text{T}} \ln \left(\frac{I_{\text{C2}}}{I_{\text{S2}}} \right) = V_{\text{T}} \ln \left(\frac{I_{\text{C1}}}{I_{\text{S1}}} \right)$$

$$\Rightarrow I_{\text{C2}} = K I_{\text{C1}} \quad (K = I_{\text{S2}}/I_{\text{S1}})$$

➤ Thus:

$$I_{\text{REF}} = I_{\text{C2}} \left[\frac{1}{\beta_2} + \frac{1}{K} \left(1 + \frac{1}{\beta_1} \right) \right]$$

➤ *Finally:*

$$I_0 = \frac{I_{\text{REF}}}{\frac{1}{\beta_2} + \frac{1}{K} \left(1 + \frac{1}{\beta_1} \right)}$$

- This is the *exact expression* of I_0 , *without making any assumptions/approximations whatsoever*
- The *only assumption* so far is that we have *neglected Early effect*, which we would include soon

➤ Now, we *make approximations/assumptions*:

1. $\beta_1 = \beta_2 = \beta$:

$$\Rightarrow I_0 = \frac{KI_{\text{REF}}}{1 + \frac{1+K}{\beta}}$$

2. $I_{S1} = I_{S2} = I_S$ ($K = 1$):

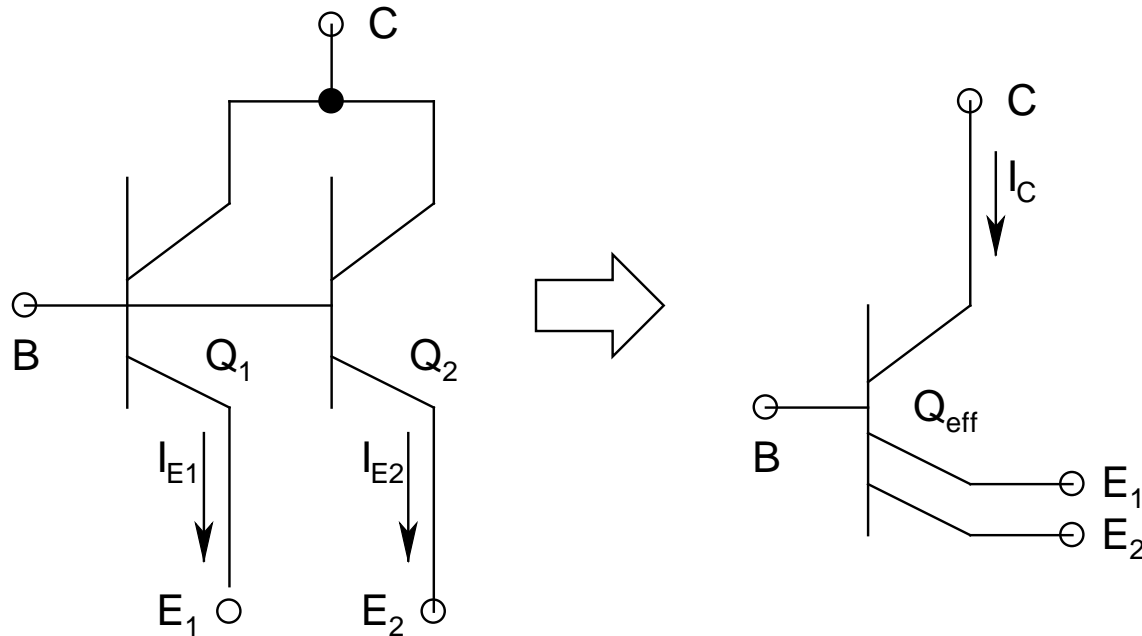
$$\Rightarrow I_0 = \frac{I_{\text{REF}}}{1 + 2/\beta}$$

3. And finally $\beta \gg 2$:

$$\Rightarrow I_0 = I_{\text{REF}} \Rightarrow \text{Current Mirror!}$$

- For this to happen, Q_1 and Q_2 must have *same β ($\gg 2$)*, and *same I_S*
- If two BJTs have *same β , I_S , and V_A* , they are known as a *matched pair*
- If $I_{S1} \neq I_{S2}$ and/or $\beta_1 \neq \beta_2$, then $I_0 \neq I_{REF}$
 - Leads to *random error (process induced)*
- If $\beta_1 = \beta_2$, but $I_{S1} \neq I_{S2}$, then $I_0 = KI_{REF}$
 - *K or 1/K can only be integers*
 - *I_0 and I_{REF} become integer multiples of each other*

- *Multi-Emitter BJT:*



➤ $I_{S1} = I_{S2} \Rightarrow I_{E1} = I_{E2} = I_E \Rightarrow I_C \approx 2I_E$

- *This does not imply that $\alpha = 2$, since there are two emitters*

- **Systematic Error:**

- *Even if Q_1 and Q_2 are perfectly matched and $\beta \gg 2$, still I_0 may not equal I_{REF} !*

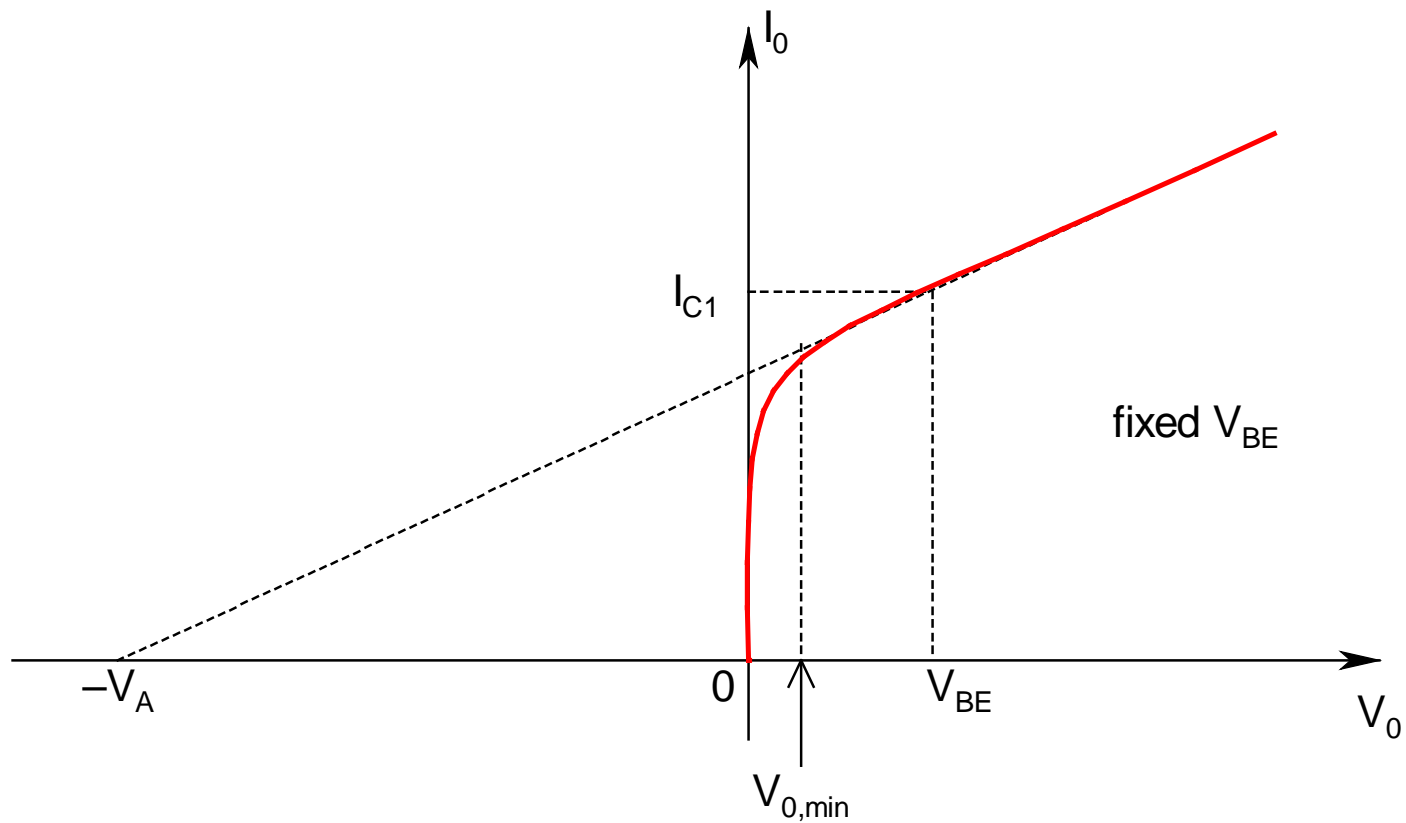
- **Recall:**

$$I_C = I_S[\exp(V_{BE}/V_T)](1 + V_{CE}/V_A)$$

- **Thus:**

$$\frac{I_{C2}}{I_{C1}} = \frac{I_0}{I_{C1}} = \frac{1 + V_{CE2}/V_A}{1 + V_{CE1}/V_A} = \frac{1 + V_0/V_A}{1 + V_{BE}/V_A}$$

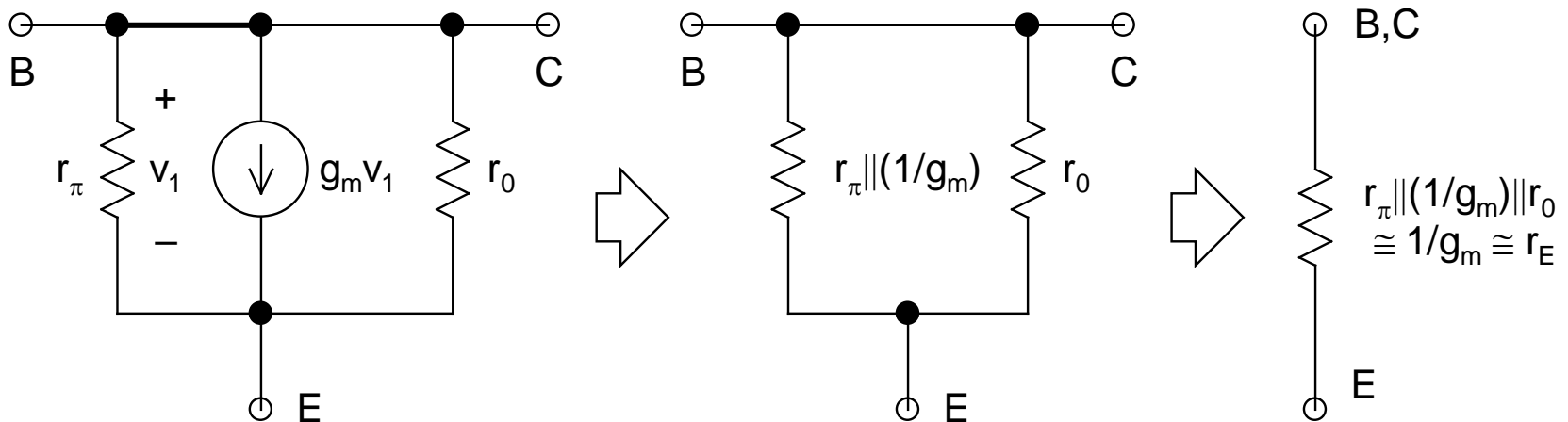
- Therefore, *$I_0 = I_{C1}$ only when $V_0 = V_{BE}$*



$$V_{0,min} = V_{CE2(SS)} = 0.2 \text{ V}$$

- **Output Resistance R_o :**

➤ First, *investigate Q_1*



- The *small-signal equivalent* consists simply of r_E , which is the same as that for a **diode**
- Hence the name *diode-connected transistor*

- *Algorithm to find R_0 :*
 - *Short all independent DC voltage sources*
 - *Open all independent DC current sources*
 - *Replace the active device by its low-frequency hybrid- π model*
 - *Excite the output terminal by a test voltage source (ac) v_t*
 - *Find the current (ac) i_t drawn from v_t*
 - *Then, $R_0 = v_t/i_t$*

- *For the complete circuit:*

- *Left part of the circuit has no source*

$$\Rightarrow v_2 = 0$$

$$\Rightarrow g_{m2}v_2 = 0$$

- Thus, $R_0 = v_t/i_t = r_{o2} = V_{A2}/I_0$

- For a *good current source*, R_0 should be as large as possible (ideally infinite)

$\Rightarrow V_{A2}$ should be as large as possible and/or I_0 should be as small as possible

